

PATENT IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: KRYLIOUK et al.

Application No.:

10/634,220

Examiner:

Filed:

August 5, 2003

Group Art Unit:

For: GROUP III-NITRIDE GROWTH ON SI SUBSTRATE USING

OXYNITRIDE INTERLAYER

CERTIFICATE UNDER 37 CFR 1.8(a)

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on _________.

Neil R. Jetter

Commissioner for Patents Post Office Box 1450 Alexandria, VA 22313-1450

Date: January 16, 2004

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to the Duty to Disclose under 37 C.F.R. §1.56, Applicants hereby disclose information that may be relevant to the Examiner's consideration of the above-identified application and the patentability of its claims.

In accordance with Rules 56, 97, and 98 of the Rules of Practice in Patent Cases (37 C.F.R. §§ 1.56, 1.97, and 1.98), Form PTO/SB/08B and copies of references cited therein are submitted for consideration by the Examiner. While the references provided in this Information Disclosure Statement may be material to patentability pursuant to 37 C.F.R. § 1.56, it is not intended to constitute an admission that any reference referred to herein is prior art for this invention unless specially designated as such. Also, in accordance with 37 C.F.R. § 1.97(g), the

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filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists.

This Information Disclosure Statement is being filed before the issuance of a first office action on the merits of the application (37 C.F.R. 1.97(b)(3)); therefore, no fee is believed to be due. However, if any fee is due, the Commissioner is authorized to charge any such fee and any additional fees due or credit any overpayment to Deposit Account No. 50-0951.

Respectfully submitted,

Neil R. Jetter, Reg

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Docket No. 5853-413

PTO/SB/08B (08-03) Approved for use through 07/31/2006. OMB 0651-0031

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			Complete if Known	
Substitute for form 1449/PTO			Application Number	10/634,220
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Filing Date	August 5, 2003
			First Named Inventor	Kryliouk et al.
			Art Unit	
			Examiner Name	
Sheet	1 of	1	Attorney Docket Number	5853-413

Examiner	Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of	T ²
Initials*	No. ¹	the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	1-
		NIKISHIN et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75:2073-2075, 1999	
		ZHANG et al., "Enhanced optical emission from GaN films grown on a silicon substrate," Applied Physics Letters, 74:1984-1986, 1999	
		LINTHICUM et al., "PROCESS ROUTES FOR LOW DEFECT-DENSITY GAN ON VARIOUS SUBSTRATES EMPLOYING PENDEO-EPITAXIAL GROWTH TECHNIQUES," MRS Internet J. Nitride Semicond. Res. 4S1, G4.9, 1999	
		STRITTMATTER et al., "Low-pressure metal organic chemical vapor deposition of GaN on silicon(111) substrates using an AlAs nucleation layer," Applied Physics Letters, 74:1242-1244, 1999	
		SANCHEZ-GARCIA et al., "Ultraviolet electroluminescence in GaN/AlGaN single-heterojunction light-emitting diodes grown on Si(111)," Journal of Applied Physics, 87:1569-1571, 2000	

Examiner	Date
Signature	Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO:

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